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Patent Abstracts of Japan

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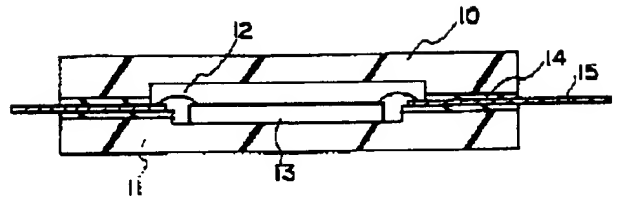
APPLICATION DATE : 29-12-93
APPLICATION NUMBER : 05349641

APPLICANT : TOSHIBA CORP;

INVENTOR : IWASE NOBUO;

INT.CL. : H01L 23/02 H01L 23/04

TITLE : SEMICONDUCTOR DEVICE



ABSTRACT : PURPOSE: To obtain a semiconductor device wherein the connection of a high speed multipin LSI of narrow pitch is enabled, and signal delay and crosstalk noise are small, by forming a low dielectric constant layer on a wiring which layer is composed of material whose permittivity is lower than that of package material or that of package bonding material.

CONSTITUTION: A package cap 10 having a recessed part for preventing the contact with bonding wires 12 is fixed on a package substrate 11. The package cap 10 is bonded to the package substrate 11 so as to sandwich a lead frame 15 via glass 14. A low dielectric constant layer 16 is formed on the peripheral surface of the lead frame 15. The low dielectric constant layer 16 formed on a wire 15 is composed of material whose dielectric constant is lower than that of the package material or that of the package bonding material.

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